

N-Channel Power MOSFET

Description

The XR46000 is a silicon N-channel enhanced power MOSFET. With low conduction loss, good switching performance and high avalanche energy, it is suitable for various power supply system, especially for AC step driving application for LED lighting.

The package type is SOT-223, which comply with the RoHS standard.

Key Parameters

V _{DSS}	600V
I _D	1.5A
P _D (T _C = 25°C)	20W
R _{DS,ON,typ}	7.0Ω

FEATURES

- Fast switching
- ESD improved capability
- Low gate charge (Typ. 7.5nC)
- Low reverse transfer capacitance (Typ. 5.0pF)

APPLICATIONS

- LED lighting applications
 - □ Downlight
 - □ High bay
 - □ Specialty
 - □ Architectural

Equivalent Circuit

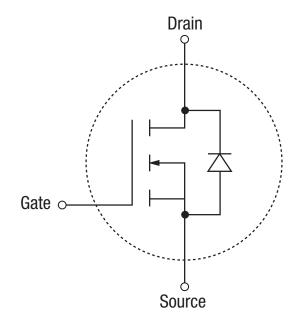
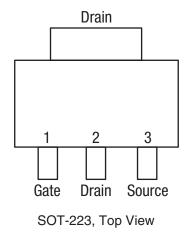


Figure 1. Equivalent Cirucit

Pin Configuration



Absolute Maximum Ratings

Stresses beyond the limits listed below may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

 $T_C = 25^{\circ}C$ unless otherwise noted.

V _{DSS} drain-to-source voltage	600V
I_D continuous drain current ($T_C = 25^{\circ}C$)	1.5A
I_D continuous drain current ($T_C = 100^{\circ}C$)	0.85A
I _{DM} pulsed drain current	6A
V _{GS} gate-to-source voltage	±30V
P_D power dissipation ($T_C = 25^{\circ}C$)	20W
P _D derating factor above 25°C	0.16W/°C
T _{STORAGE} storage temperature range	-65°C to 150°C
E _{AS} single pulse avalanche energy	80mJ
NOTE:	

Unless otherwise noted, all tests are pulsed tests at the specified temperature, therefore: $T_J = T_C = T_A$.

Operating Conditions

T _J operating junction temperature	150°C
T _A operating ambient temperature	40°C to 85°C



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Electrical Characteristics

 $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF Charac	cteristic					
BV _{DSS}	Drain to source breakdown voltage	$V_{GS} = 0V, I_D = 250\mu A$				V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown voltage temperature coefficient	I _D = 250μA, reference 25°C		0.71		V/°C
I _{DSS}		V _{DS} = 600V, V _{GS} = 0V, T _A = 25°C	25			
	Drain to source leakage current	V _{DS} = 600V, V _{GS} = 0V, T _A = 125°C			250	μA
I _{GSS(F)}	Gate to source forward leakage	V _{GS} = 30V		12		
I _{GSS(R)}	Gate to source reverse leakage	V _{GS} = -28V			-12	μA
ON Charact	eristic (pulse width tp \leq 380 μ s, $\delta \leq$ 2%)					
R _{DS(ON)}	Drain to source on-resistance	$V_{GS} = 10V, I_D = 0.75A$		7.0	8.0	Ω
V _{GS(TH)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
Dynamic Ch	naracteristic					
9fs	Forward transconductance	$V_{DS} = 15V, I_D = 0.75A$		1.0		s
C _{iss}	Input capacitance			170		pF
C _{oss}	Output capacitance	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		27		
C _{rss}	Reverse transfer capacitance			5		
Resistive Sv	witching Characteristic					
t _{d(ON)}	Turn-on delay time			8		
t _r	Rise time	$I_D = 1.5A$, $V_{DD} = 300V$, $V_{GS} = 10V$,		30		- ns
t _{d(OFF)}	Turn-off delay time	$R_G = 4.7\Omega$		22		
t _f	Fall time			55		
Qg	Total gate charge			7.5		
Q _{gs}	Gate to source charge	$I_D = 1.5A$, $V_{DD} = 480V$, $V_{GS} = 10V$		1.7		nC
Q _{gd}	Gate to drain "Miller" charge			4.0		
Source-Drai	in Diode Characteristics (pulse width tp ≤	380us, δ ≤ 2%)				
I _S	Continuous source current (body diode)				1.5	Α
I _{SM}	Maximun source current (body diode)				6.0	
V _{SD}	Diode forward voltage	I _S = 1.5A, V _{GS} =0V			1.5	V
T _{rr}	Reverse recovery time			530		ns
Q _{rr}	Reverse recovery charge	$I_D = 1.5A$, $T_J = 25$ °C, $dI_F/dt = 100A/\mu s$, $V_{GS} = 0V$		1100		nC
I _{RRM}	Reverse recovery current			4.4		А



Typical Performance Characteristics

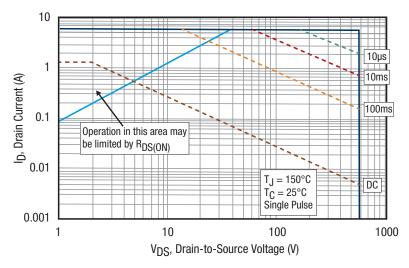


Figure 2. Safe Operating Area

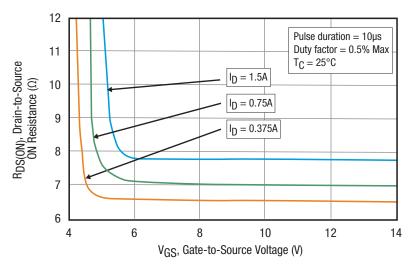


Figure 3. Typical Drain-to-Source ON Resistance vs. Gate Voltage and Drain Current

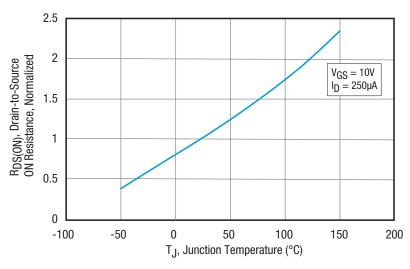
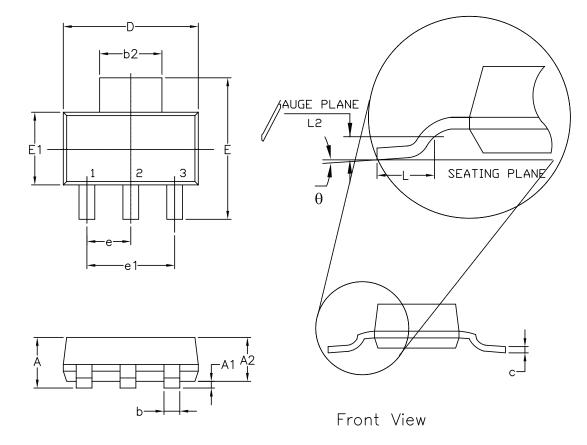


Figure 4. Typical Drain-to-Source ON Resistance vs. Junction Temperature



Package Description

Top View



Side View

3 Pin SOT-223 JEDEC TO-261 Variation AA						
SYMBOLS	DIMENSIONS IN MM (Control Unit)			DIMENSIONS IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	_	_	1.80	_	_	0.071
A1	0.02	_	0.10	0.001	_	0.004
A2	1.50	1.60	1.70	0.060	0.063	0.067
b	0.66	0.76	0.84	0.026	0.030	0.033
b2	2.90	3.00	3.10	0.114	0.118	0.122
С	0.23	0.30	0.35	0.010	0.012	0.014
D	6.30	6.50	6.70	0.248	0.256	0.264
E	6.70	7.00	7.30	0.264	0.276	0.287
E1	3.30	3.50	3.70	0.130	0.138	0.146
е	2.30 BSC			C).091 B	SC
e1	4.60 BSC		C).182 B	SC	
L	0.75	_	_	0.030	_	_
L2	0.25 BSC			0	.010 BS	SC
θ	0°		10°	0°	_	10°
N	3				3	



Ordering Information

Part Number	Operating Temperature Range	Environmental Rating	Package	Packaging Method
XR46000ESE			SOT-223	Bulk
XR46000ESETR	-40°C ≤ T _J ≤ 150°C	RoHS compliant and Green(1)	SOT-223	Tape and reel
XR46000ECF			Dice	Wafer

NOTE:

Revision History

Revision	Date	Description
1A	Aug 2016	Initial release



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